

**Publisher's Note: "Memory effect of oxide/SiC:O/oxide sandwiched structures" [Appl. Phys. Lett. 84, 2094 (2004)]**

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Citation: [Applied Physics Letters](#) **84**, 4815 (2004); doi: 10.1063/1.1761633

View online: <http://dx.doi.org/10.1063/1.1761633>

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(Received 20 April 2004; published online 21 May 2004)

[DOI: 10.1063/1.1761633]

This article was originally published with errors in the affiliation for T. C. Chang. AIP apologizes for these errors; the correct version of T. C. Chang's affiliation appears above. All online versions of the article have been corrected.

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